

ECH8695R

Power MOSFET

for 1-2 Cells Lithium-ion Battery Protection 24 V, 9.1 mΩ, 11 A, Dual N-Channel



ON Semiconductor®

www.onsemi.com

This Power MOSFET features a low on-state resistance. This device is suitable for applications such as power switches of portable machines. Best suited for 1-2 cells Lithium-ion Battery applications.

Features

- Low On-Resistance
- 2.5 V drive
- Common-Drain Type
- ESD Diode-Protected Gate
- Built-in Gate Protection Resistor
- Pb-Free, Halogen Free and RoHS compliance

Typical Applications

- 1-2 cells Lithium-ion Battery Charging and Discharging Switch

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at $T_a = 25^\circ\text{C}$ (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V_{DS}	24	V
Gate to Source Voltage	V_{GS}	± 12.5	V
Drain Current (DC)	I_D	11	A
Drain Current (Pulse) $PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$	I_{DP}	60	A
Power Dissipation Surface mounted on ceramic substrate ($900 \text{ mm}^2 \times 0.8 \text{ mm}$) 1 unit	P_D	1.4	W
Total Dissipation Surface mounted on ceramic substrate ($900 \text{ mm}^2 \times 0.8 \text{ mm}$)	P_T	1.5	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to $+150$	$^\circ\text{C}$

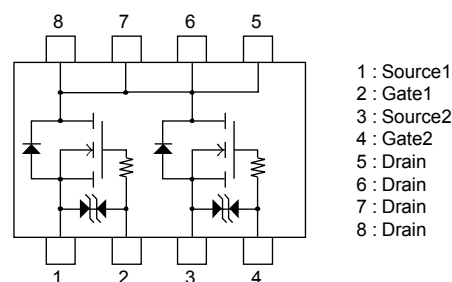
Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

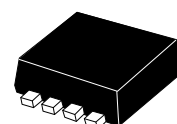
Parameter	Symbol	Value	Unit
Junction to Ambient Surface mounted on ceramic substrate ($900 \text{ mm}^2 \times 0.8 \text{ mm}$) 1 unit	$R_{\theta JA}$	89.2	$^\circ\text{C/W}$

V_{DS}	$R_{DS(on)}$ Max	I_D Max
24 V	9.1 mΩ @ 4.5 V	11 A
	9.5 mΩ @ 4.0 V	
	11.5 mΩ @ 3.1 V	
	13.3 mΩ @ 2.5 V	

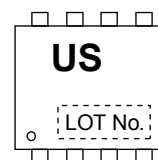
ELECTRICAL CONNECTION N-Channel



MARKING



SOT-28FL / ECH8



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

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ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 2)

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	V(BR)DSS	I _D = 1 mA, V _{GS} = 0 V	24			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±8 V, V _{DS} = 0 V			±1	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = 10 V, I _D = 1 mA	0.5		1.3	V
Forward Transconductance	g _{FS}	V _{DS} = 10 V, I _D = 5 A		6.5		S
Static Drain to Source On-State Resistance	R _{DS(on)}	I _D = 5 A, V _{GS} = 4.5 V	5.6	7.0	9.1	mΩ
		I _D = 5 A, V _{GS} = 4.0 V	5.8	7.3	9.5	mΩ
		I _D = 5 A, V _{GS} = 3.1 V	6.5	8.2	11.5	mΩ
		I _D = 2.5 A, V _{GS} = 2.5 V	7.6	9.5	13.3	mΩ
Turn-ON Delay Time	t _{d(on)}	See Fig. 1 (Note 3)		300		ns
Rise Time	t _r			320		ns
Turn-OFF Delay Time	t _{d(off)}			19.7		μs
Fall Time	t _f			22.3		μs
Turn-ON Delay Time	t _{d(on)}	See Fig. 2 (Note 3)		300		ns
Rise Time	t _r			320		ns
Turn-OFF Delay Time	t _{d(off)}			1,240		μs
Fall Time	t _f			370		μs
Total Gate Charge	Q _g	V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 11 A		10		nC
Gate to Source Charge	Q _{gs}			1.6		nC
Gate to Drain "Miller" Charge	Q _{gd}			1.5		nC
Forward Diode Voltage	V _{SD}	I _S = 11 A, V _{GS} = 0 V		0.77	1.2	V

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Note 3 : The fall switching time is dependent on the input pulse width.

Fig.1 Switching Time Test Circuit 1

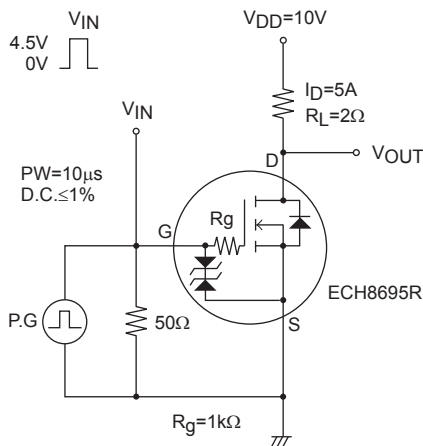
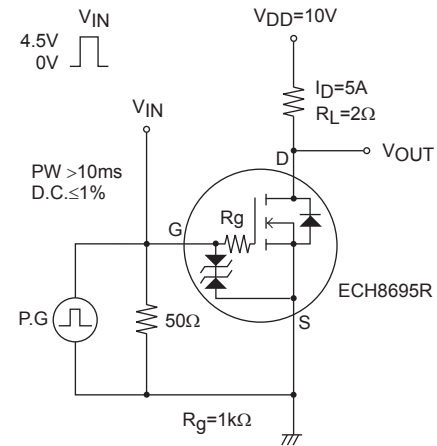
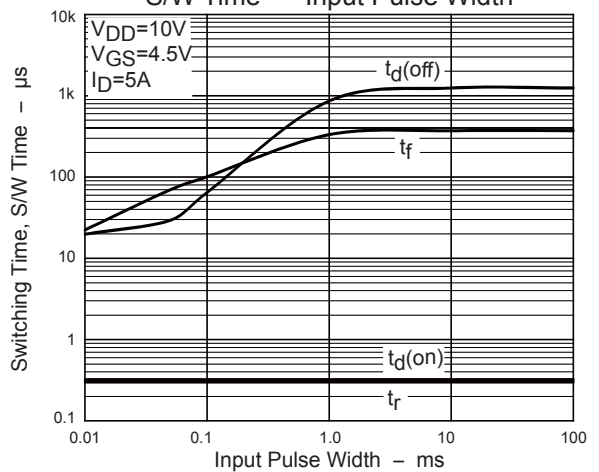
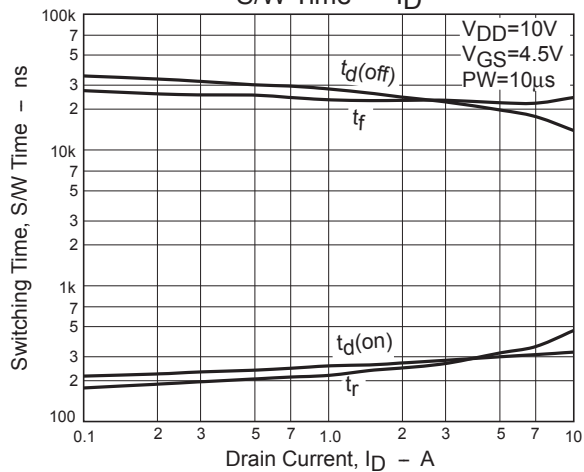
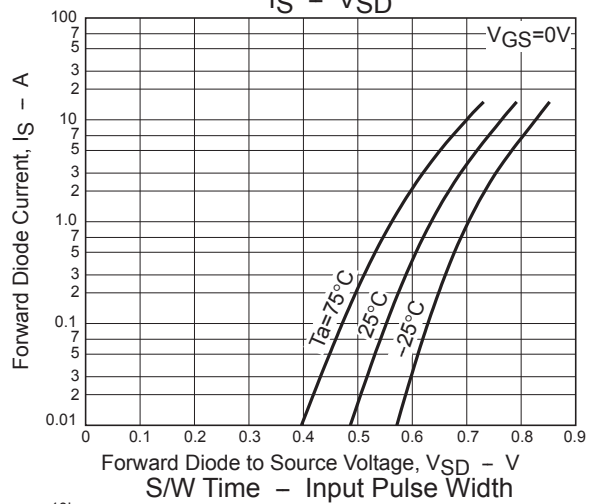
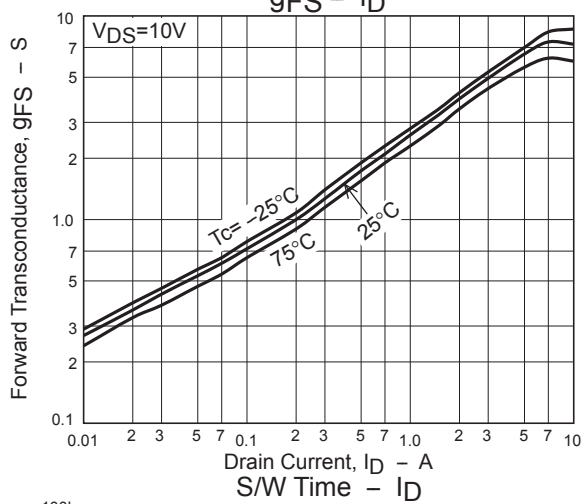
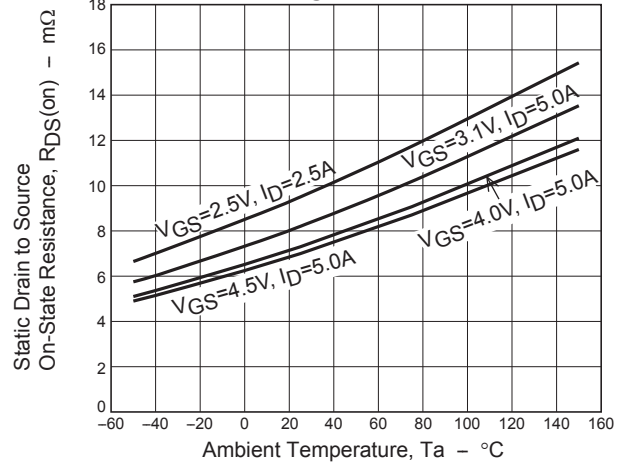
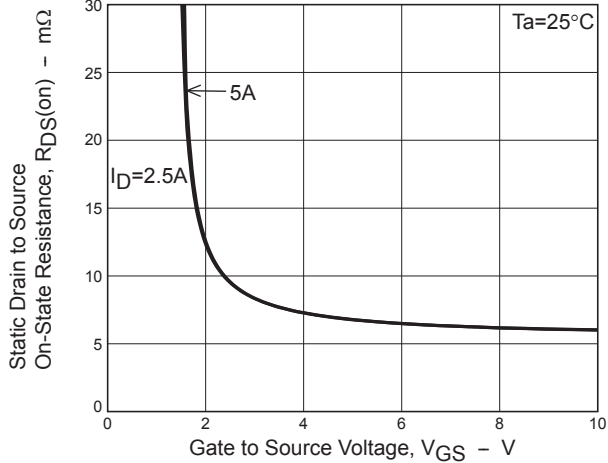
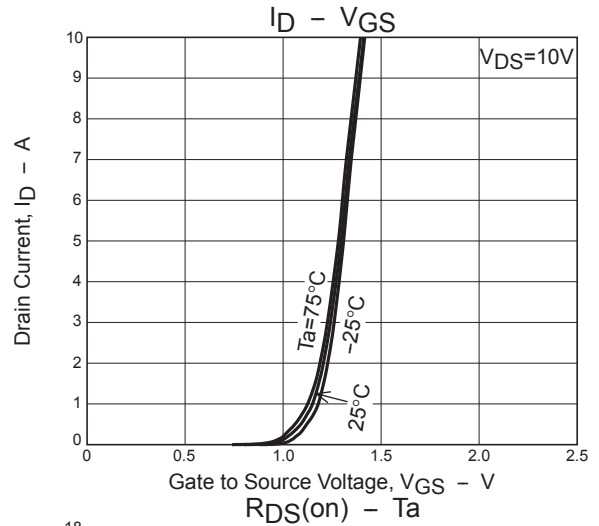
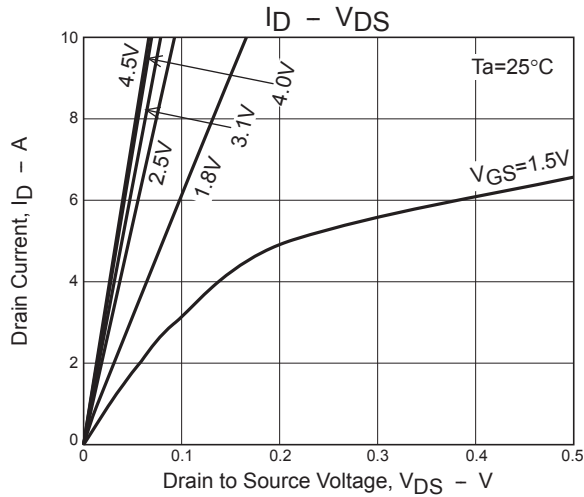


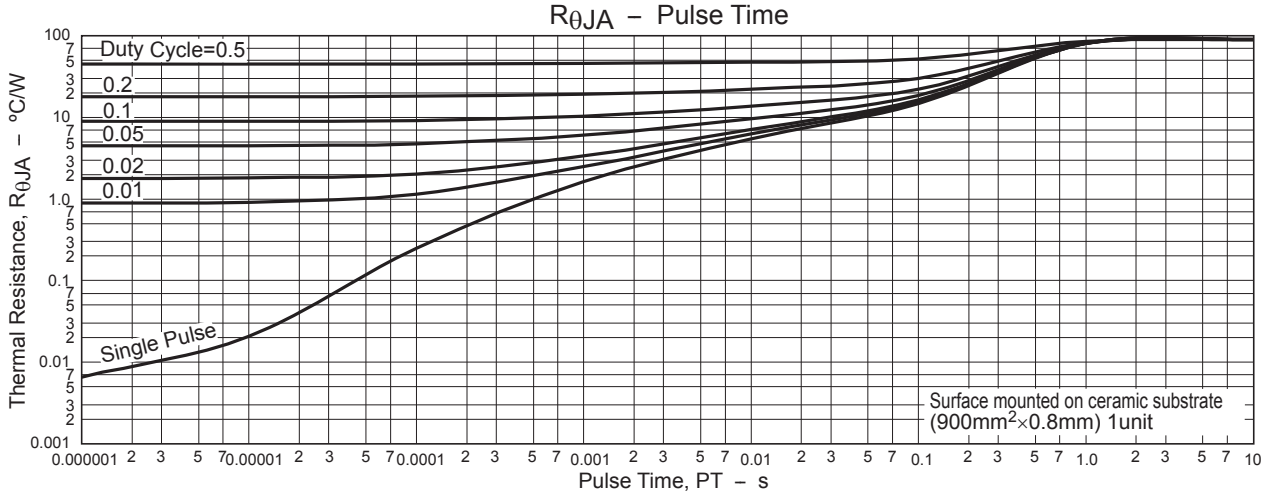
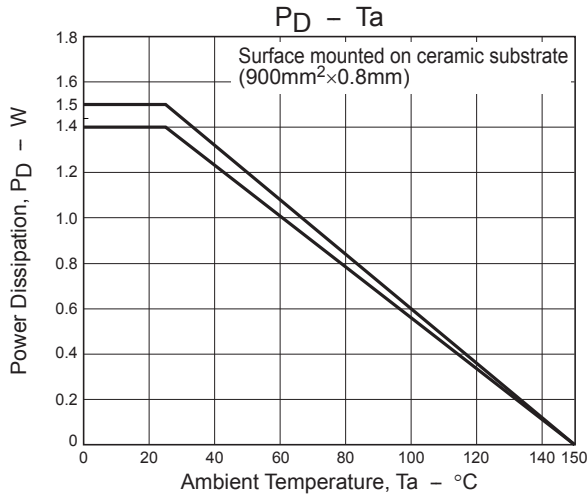
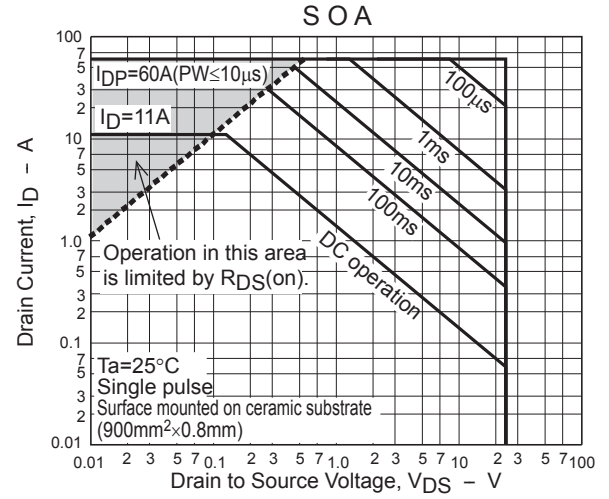
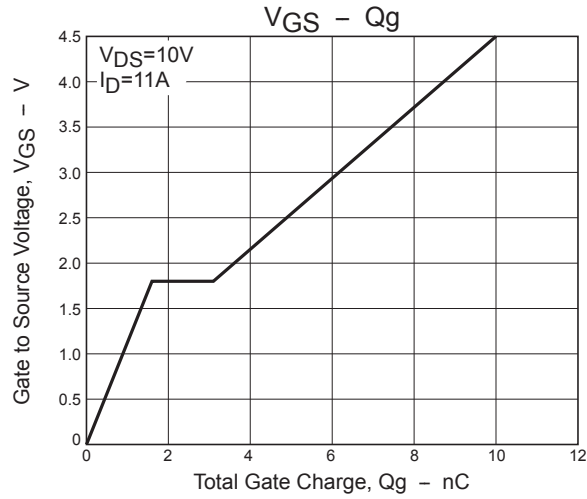
Fig.2 Switching Time Test Circuit 2



ECH8695R



ECH8695R

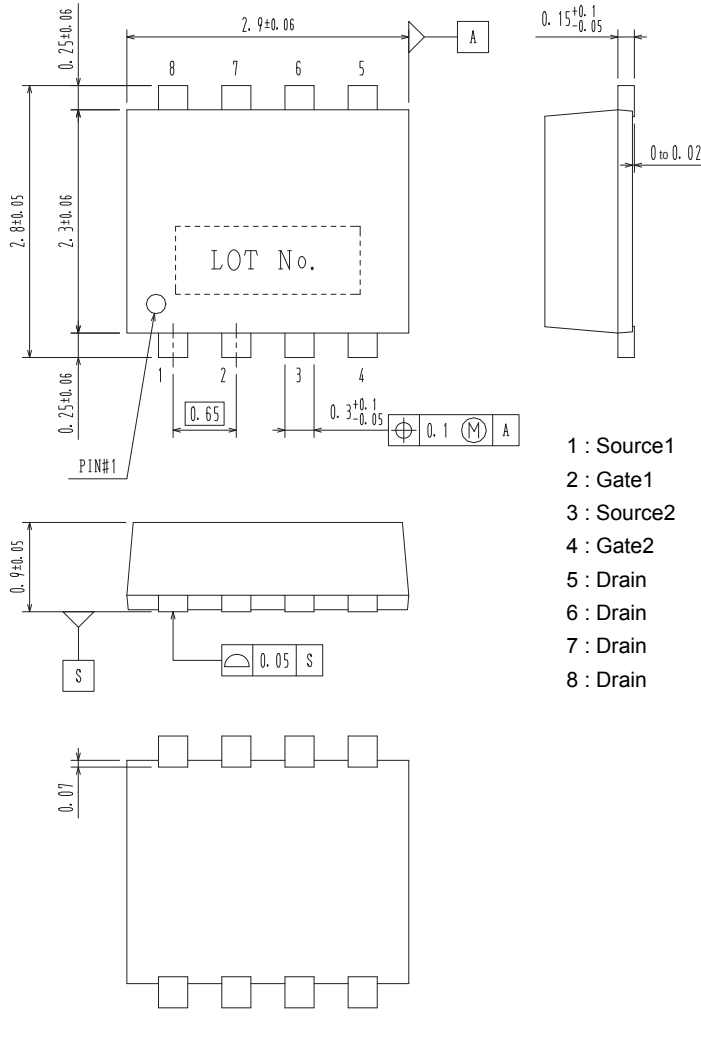


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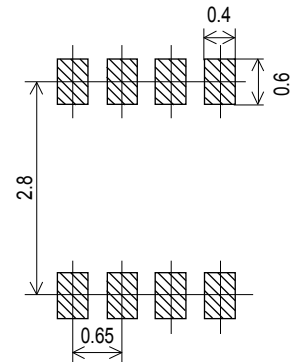
PACKAGE DIMENSIONS

unit : mm

SOT-28FL / ECH8
CASE 318BF
ISSUE O



Recommended Soldering Footprint



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
ECH8695R-TL-W	US	SOT-28FL / ECH8 (Pb-Free / Halogen Free)	3,000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the ECH8695R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects. Please contact sales for use except the designated application.

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